

W32P3C

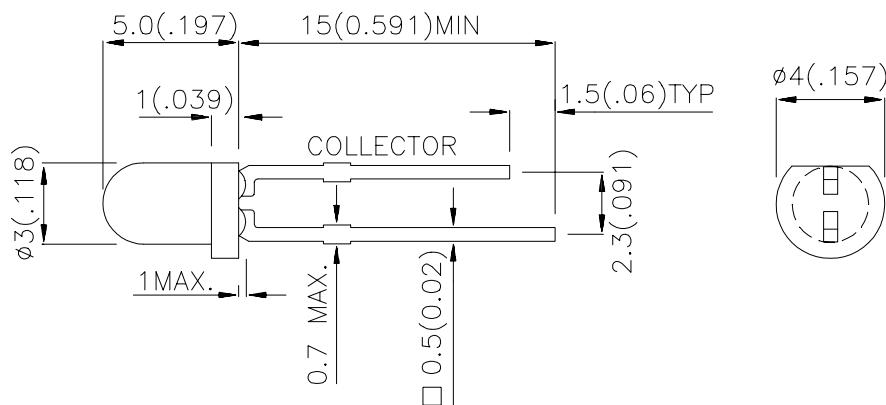
Features

- MECHANICALLY AND SPECTRALLY MATCHED TO THE W34 SERIES INFRARED EMITTING LED LAMP.
- WATER CLEAR LENS.

Description

P3 Made with NPN silicon phototransistor chips.

Package Dimensions



Notes:

1. All dimensions are in millimeters (inches).
2. Tolerance is $\pm 0.25(0.01")$ unless otherwise noted.
3. Lead spacing is measured where the lead emerge package.
4. Specifications are subject to change without notice.

Electrical / Optical Characteristics at $T_A=25^\circ C$

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Condition
V_{BRCEO}	Collector-to-Emitter Breakdown Voltage	30	-	-	V	$I_C=100\mu A$, $E_e=0mW/cm^2$
V_{BRECO}	Emitter-to-Collector Breakdown Voltage	5	-	-	V	$I_E=100\mu A$, $E_e=0mW/cm^2$
$V_{CE(SAT)}$	Collector-to-Emitter Saturation Voltage	-	-	0.8	V	$I_C=2mA$, $E_e=20mW/cm^2$
I_{CEO}	Collector Dark Current	-	-	100	nA	$V_{CE}=10V$, $E_e=0mW/cm^2$
T_R	Rise Time (10% to 90%)	-	3	-	μs	$V_{CE}=5V$, $I_C=1mA$, $R_L=1000\Omega$
T_F	Fall Time (90% to 10%)	-	3	-	μs	
$I_{(ON)}$	On State Collector Current	0.1	0.5	-	mA	$V_{CE}=5V$, $E_e=1mW/cm^2$, $\lambda=940nm$

Absolute Maximum Ratings at $T_A=25^\circ C$

Parameter	Maximum Rating
Collector-to-Emitter Breakdown Voltage	30V
Emitter-to-Collector Breakdown Voltage	5V
Power Dissipation at (or below) 25°C Free Air Temperature	100mW
Operating Temperature Range	-40°C ~ +85°C
Storage Temperature Range	-40°C ~ +85°C
Lead soldering Temperature (>5mm for 5sec)	260°C